

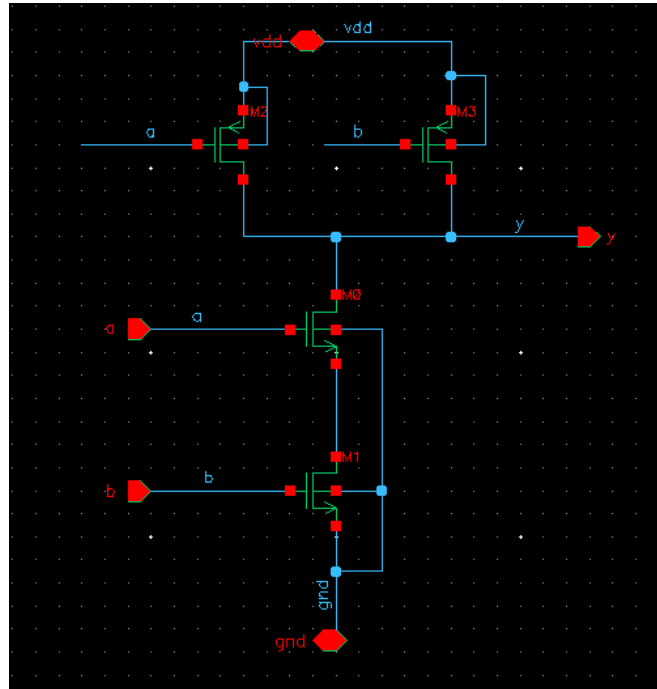
Intro to VLSI

Lab Task 1 – NAND gate

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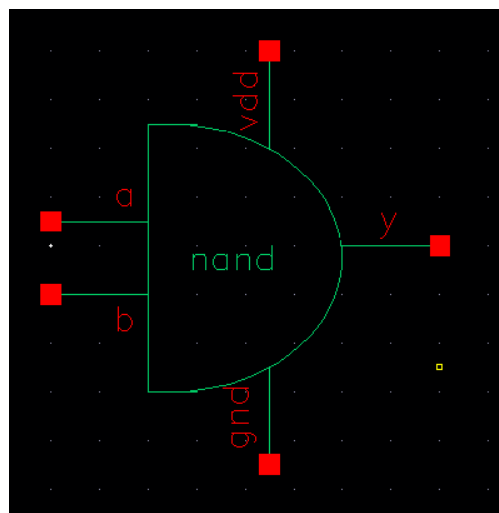
(20171049)

I have designed the NAND gate schematic which is as shown in figure below:



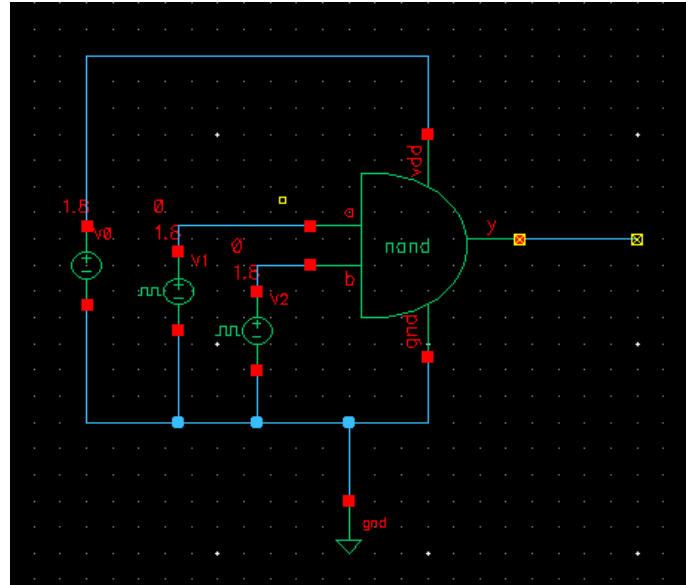
Schematic of NAND gate

Instead of applying power sources, I have attached pins in the schematic to create a symbol for it and then using it to test the working of the NAND gate. So the symbol is created and shown below:



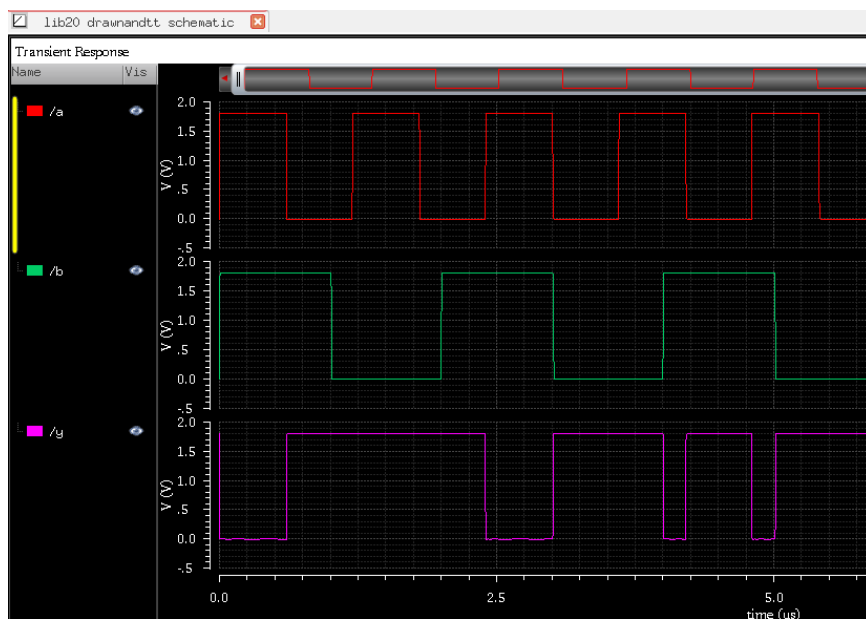
Symbol of NAND gate

Now, we have to test our symbol, so we add it in a new schematic, apply power sources and make the connections properly.



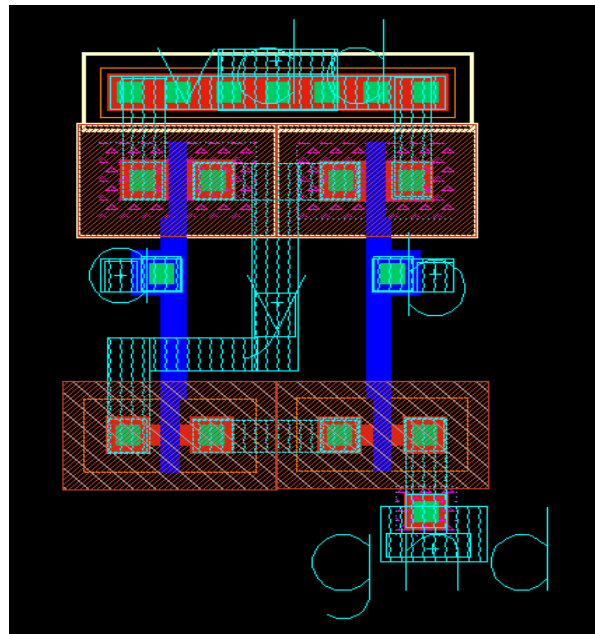
Circuit Diagram of NAND gate with symbol

The results obtained from the NAND gate symbol are shown below, and it is verified that our NAND gate is working properly.



Inputs – a (red) & b (green). Output – y (purple)

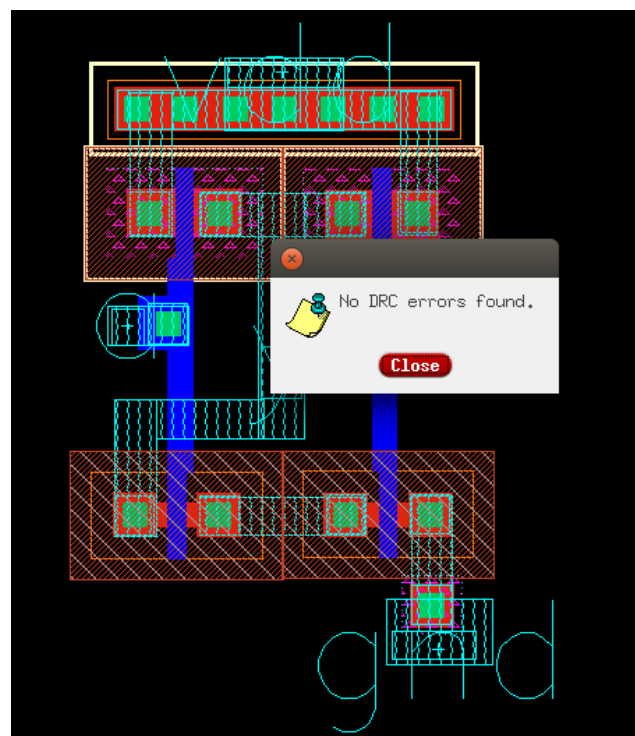
Now we will make the layout for our NAND gate, and draw it in accordance with the lambda rules. The layout formed is shown below:



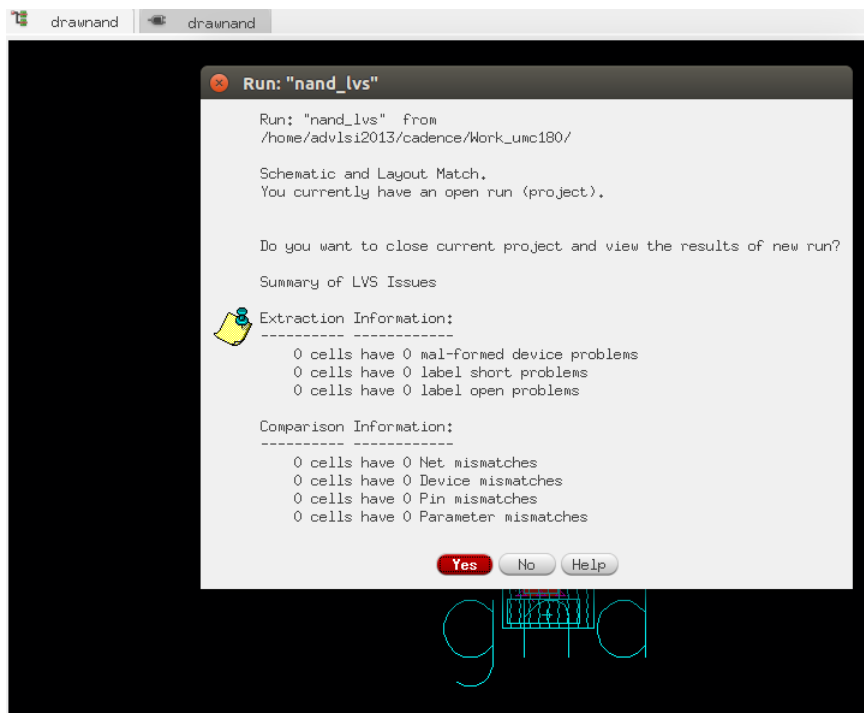
Layout of NAND gate

We have minimized the area and it is found that the minimized area is $4.311\mu\text{m} \times 5.953\mu\text{m} = 25.663 \mu\text{m}^2$.

The results of the DRC test and LVS test were successful for the layout formed, i.e., there were no errors in the layout and also it is now matched with the schematic which we had drawn earlier.

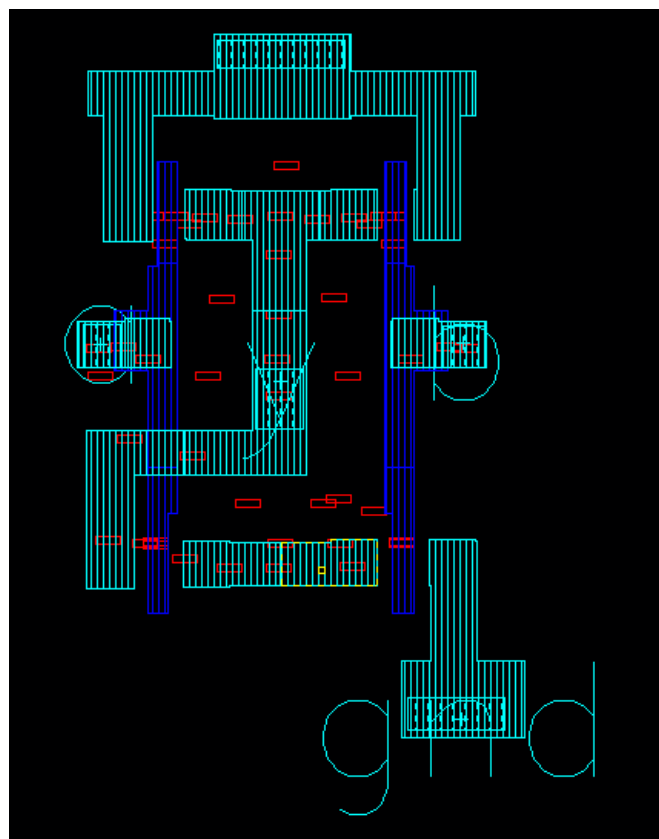


Result of DRC test (successful)



Result of LVS test (successful)

Now, the RCX test is run to generate the extracted view of the layout, which shows the presence of various parasitic capacitances and resistances and it is shown below:



Extracted view of the layout with parasitic capacitances and resistances

We can now ensure that our layout drawn also gives correct results. So, changing the hierarchy of our symbol from schematic to layout, the following results were obtained and we can see that the output is coming correctly from the transient analysis of the circuit. Also we can see the presence of multiple resistances, capacitances, and nodes in the results, which were not in the schematic.

```

Peak resident memory used = 25.1 Mbytes.

Time for EDB Visiting: CPU = 1 ms, elapsed = 978,947 us.
Time accumulated: CPU = 136,978 ms, elapsed = 211,109 ms.
Peak resident memory used = 25.4 Mbytes.

Warning from spectre during initial setup.
WARNING (CMI-2426): IO.M3: 'Cdscd' = -28,83e-06 is negative.
WARNING (CMI-2426): IO.M0: 'Pdiblc2' = -37,9166e-03 is negative.
WARNING (CMI-2426): IO.M0: 'Cdscd' = -500e-06 is negative.

Circuit inventory:
  nodes 19
  bsim3v3 4
  capacitor 63
  resistor 14
  vsource 3

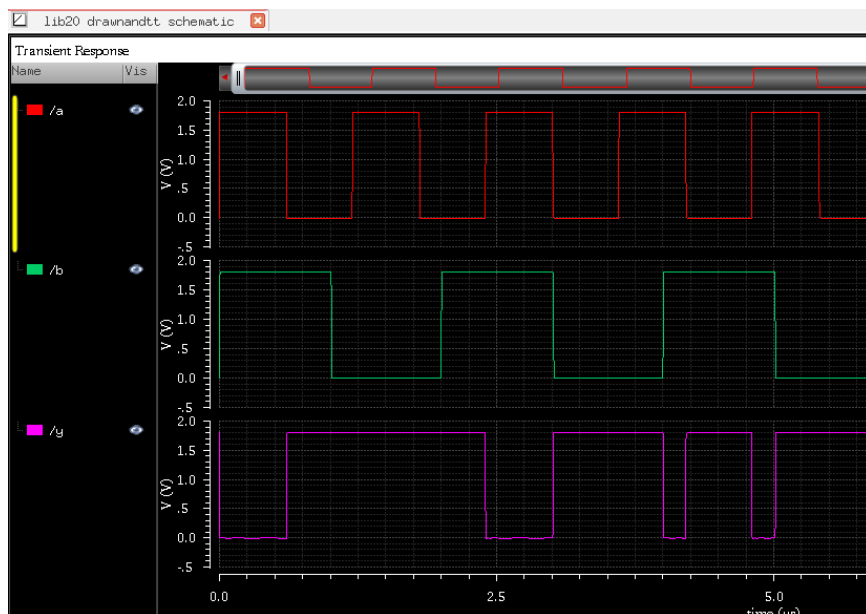
Warning from spectre during initial setup.
WARNING (CMI-2426): IO.M3: 'Cdscd' = -28,83e-06 is negative.
WARNING (CMI-2426): IO.M0: 'Pdiblc2' = -37,9166e-03 is negative.
  Further occurrences of this warning will be suppressed.
Notice from spectre.
  8 warnings suppressed.

Time for parsing: CPU = 1 ms, elapsed = 5,04303 ms.
Time accumulated: CPU = 137,978 ms, elapsed = 216,346 ms.
Peak resident memory used = 26.2 Mbytes.

Entering remote command mode using MPSC service (spectre, ipi, v0.0,

Warning from spectre.
WARNING (SPECTRE-16707): Only tran supports psfxt format, result

```



Inputs – a (red) & b (green). Output – y (purple)

Now, we compare the results of the original schematic with that of the results from layout hierarchy. Again transient analysis is done and results are as shown:

```

/home/advlsi2013/simulation/drawnandtt/spectre/schemat
File Help cadence

Warning from spectre in 'drawnand': 'IO', during hierarchy flattening.
WARNING (SFE-30): "input.scs" 35: IO.M0: 'nf' is not a valid param
WARNING (SFE-30): "input.scs" 35: IO.M0: 'mis_flag' is not a valid
WARNING (SFE-30): "input.scs" 35: IO.M0: 'nf' is not a valid param
WARNING (SFE-30): "input.scs" 37: IO.M1: 'nf' is not a valid param
WARNING (SFE-30): "input.scs" 37: IO.M1: 'mis_flag' is not a valid
Further occurrences of this warning will be suppressed.

Time for Elaboration: CPU = 23,997 ms, elapsed = 24,0409 ms.
Time accumulated: CPU = 109,982 ms, elapsed = 323,628 ms.
Peak resident memory used = 25 Mbytes.

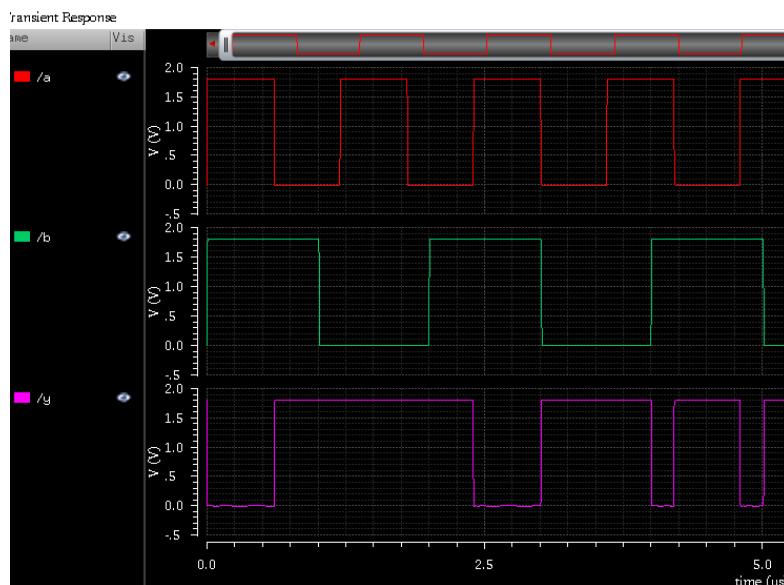
Time for EDB Visiting: CPU = 0 s, elapsed = 509,024 us.
Time accumulated: CPU = 109,982 ms, elapsed = 324,326 ms.
Peak resident memory used = 25,3 Mbytes.

Warning from spectre during initial setup.
WARNING (CMI-2426): IO.M2: 'Cdscd' = -28,83e-06 is negative.
WARNING (CMI-2426): IO.M1: 'Pdiblc2' = -37,9166e-03 is negative.
WARNING (CMI-2426): IO.M1: 'Cdscd' = -500e-06 is negative.

Circuit inventory:
  nodes 5
  bsim3v3 4
  vsource 3

Warning from spectre during initial setup.
WARNING (CMI-2426): IO.M2: 'Cdscd' = -28,83e-06 is negative.
WARNING (CMI-2426): IO.M1: 'Pdiblc2' = -37,9166e-03 is negative.
Further occurrences of this warning will be suppressed.
Notice from spectre.
8 warnings suppressed.

```



Inputs – a (red) & b (green). Output – y (purple)

So, the comparison between the results of the layout and the schematic of the NAND gate are approximately same. There are very little distortions in the output waveforms of the layout which is not in the case of schematic. So, the layout and the schematic are successfully verified theoretically also. Thus our NAND gate design is successfully completed. Also the area of the layout was minimized and was found to be 25.663 μm^2 .